Yongsen

YEGM40BF1204HZ

IGBT Power Module

Features:

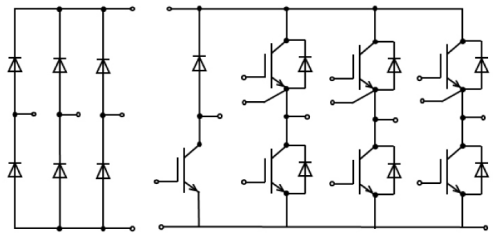
- V_{CE}=1200V I_C=35A
- Low $V_{CE(sat)}$
- V_{CEsat} with positive temperature coefficient
- Maximum junction temperature 150℃
- Isolation Type Package

Applications:

- The inverter
- Motor control and drives

Package Type & Internal Circuit

L4



Internal Circuit

Maximum Rated Values (IGBT,Inverter)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	V_{EC}=0 V,I_C=1mA,T_{vj}=25 ℃	1200	V
I_C	Continuous Collector Current	T_C=80℃,T_{vjmax}=150 ℃	40	A
I_{CRM}	Peak Collector Current	I_{CRM}=2I_C	80	A
V_{GES}	Gate-Emitter Voltage	T_{vj}=25 ℃	±30	V
P_{tot}	Total Power Dissipation	T_C=25 ℃,T_{vjmax}=150 ℃	200	W

Characteristics Values (IGBT Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	IC=40 A, V_{GE}=15 V, T_{vj}=25 ℃		1.83	2.5	V
		IC=40 A, V_{GE}=15 V, T_{vj}=125 ℃		2.13	2.7	V
$V_{GE(th)}$	Gate Threshold Voltage	I_C=2 mA,V_{CE}=V_{GE},T_{vj}= 25 ℃	5.2	6.2	7.0	V
C_{ies}	Input capacitance	f = 1 MHz, T_{vj}= 25°C, V_{CE} = 25 V, V_{GE}= 0 V			3.11	nF
C_{res}	Reverse transfer capacitance				103	pF
I_{CES}	Collector-Emitter Cut-off Current	V_{CE}=1200 V, V_{GE}=0 V, T_{vj}=25 ℃			1.2	mA
I_{GES}	Gate-Emitter Leakage Current	V_{CE}=0 V, V_{GE}=20V, T_{vj}=25 ℃			410	nA
$t_{d(on)}$	Turn-on Delay Time, Inductive Load	IC=40 A,V_{CE}=600 V V_{GE}=±15 V R_G=15Ω T_{vj}=25 ℃		50		ns
t_r	Rise Time, Inductive Load			48		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load			200		ns
t_f	Fall Time, Inductive Load			156		ns
E_{on}	Turn-on Energy Loss per Pulse			2.64		mJ
E_{off}	Turn-off Energy Loss per Pulse			1.87		mJ
$t_{d(on)}$	Turn-on Delay Time, Inductive Load	IC=40 A,V_{CE}=600 V V_{GE}=±15 V R_G=15Ω T_{vj}=125 ℃		55		ns
t_r	Rise Time, Inductive Load			60		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load			240		ns
t_f	Fall Time, Inductive Load			240		ns
E_{on}	Turn-on Energy Loss per Pulse			3.22		mJ
E_{off}	Turn-off Energy Loss per Pulse			3.01		mJ
R_{thJC}	Thermal resistance, junction to case	per IGBT			0.65	K/W
$T_{vj\ op}$	Temperature under switching conditions		-40		125	℃
I_{sc}	SC	V_{GE}≤15V, V_{CE}=600V, t_p≤10μS, T_{vj}=125℃, V_{CEmax}=V_{CES}-L_{sCE} ·di/dt		160		A

Maximum Rated Values (Diode Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	T_{vj}= 25 ℃		1200		V
I_F	Continuous DC Forward Current			35		A
I_{FRM}	Repetitive Peak Forward Current	t_P=1 ms		70		A
I^2t	I^2t Value	V_R=0 V, t_P=10 ms, T_{vj}=125 ℃		220		A^2s

Characteristic Values (Diode Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage	IF=40 A, V_{CE}=0 V,T_{vj}= 25 ℃		1.9	2.5	V
		IF=40 A, V_{CE}=0 V,T_{vj}=125 ℃		1.9		V
t_{rr}	Reverse Recovery time	IF=40 A,V_R=600 V -di/dt=100A/us T_{vj}=25 ℃, V_{GE}=-15V		170		ns
Q_r	Recovered Charge			0.98		uC
E_{rec}	Reverse Recovery Energy			0.35		mJ
t_{rr}	Reverse Recovery time	I_F=35A,V_R=600 V -di/dt=100A/us T_{vj}=125 ℃ V_{GE}=-15V		205		ns
Q_r	Recovered Charge			1.09		uC
E_{rec}	Reverse Recovery Energy			0.36		mJ
R_{thJC}	Thermal resistance, junction to case	per Diode			1.0	K/W
$T_{vj\ op}$	Temperature under switching conditions		-40		125	℃

Maximum Rated Values (Diode Rectifier)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{RRM}	Repetitive peak reverse voltage	T_{vj}=25 ℃		1800		V
I_{FRMSM}	Maximum RMS forward current per chip	T_c=80 ℃		70		A
I_{RMSM}	Maximum RMS current at rectifier chip	T_c=80 ℃		70		A
I_{FSM}	Surge forward current	t_p=10ms T_{vj}=25 ℃		420		A
I^2t	I^2t-value	t_p=10ms T_{vj}=25 ℃		880		A^2S
I_{FSM}	Surge forward current	t_p=10ms T_{vj}=125 ℃		360		A
I^2t	I^2t-value	t_p=10ms T_{vj}=125 ℃		600		A^2S

Characteristic Values (Diode Rectifier)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward voltage	T_c=25 ℃		0.9		V
I_R	Reverse current	T_{vj}=125 ℃ V_R=1800V		1.1		mA
R_{thjc}	Thermal resistance junction to case	T_c=25 ℃			1.5	K/W
T_{vjop}	Temperature under switching conditions		-40		125	℃

Maximum Rated Values (IGBT Brake-Chopper)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{CES}	Collector-emitter voltage	T_{vj}=25℃		1200		V
I_C	Continuous Collector Current	TC = 80° C, Tvj max = 150℃		25		A
I_{CRM}	Peak Collector Current	I_{CRM}=2I_C		50		A
V_{GES}	Gate-Emitter Voltage	T_{vj}=25℃	-20		20	V

Characteristic Values (IGBT Brake-Chopper)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=25 A, V_{GE}=15 V, T_{vj}=25 ℃	1.7	1.85	2.5	V
		I_C=25 A, V_{GE}=15 V, T_{vj}=125 ℃		2.53	2.7	V
$V_{GE(th)}$	Gate Threshold Voltage	I_C=5.0 mA,V_{CE}=V_{GE},T_{vj}= 25 ℃	5.2	6.0	6.5	V
I_{CES}	Collector-Emitter Cut-off Current	V_{CE}=1200 V, V_{GE}=0 V, T_{vj}=25 ℃			20	uA
I_{GES}	Gate-Emitter Leakage Current	V_{CE}=0 V, V_{GE}=15 V, T_{vj}=25 ℃			200	nA
C_{ies}	Input capacitance	f = 1 MHz, T_{vj}= 25°C, V_{CE} = 25 V, V_{GE}= 0 V		2.15		nF
C_{res}	Reverse transfer capacitance			72.3		pF
$t_{d(on)}$	Turn-on Delay Time, Inductive Load	I_C=25 A,V_{CE}=600 V V_{GE}=±15 V R_{Gon}=20Ω T_{vj}=25 ℃		138		ns
t_r	Rise Time, Inductive Load			94		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load			220		ns
t_f	Fall Time, Inductive Load			152		ns
E_{on}	Turn-on Energy Loss per Pulse			3.53		mJ
E_{off}	Energy Loss per Pulse			1.23		mJ
$t_{d(on)}$	Turn-on Delay Time, Inductive Load	I_C=25 A,V_{CE}=600 V V_{GE}=±15 V R_{Gon}=20Ω T_{vj}=125 ℃		116		ns
t_r	Rise Time, Inductive Load			114		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load			264		ns
t_f	Fall Time, Inductive Load			244		ns
E_{on}	Turn-on Energy Loss per Pulse			4.41		mJ
E_{off}	Turn-off Energy Loss per Pulse			1.81		mJ
R_{thJC}	Thermal resistance, junction to case	per IGBT			1.45	K/W
$T_{vj\ op}$	Temperature under switching conditions		-40		150	°C
I_{sc}	SC	V_{GE}≤15V, V_{CE}=600V, tp≤10μS, T_{vj}=150℃,VCE_{max}=V_{CES}-L_{sCE} ·di/dt		100		A

Maximum Rated Values (Diode Brake-Chopper)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	T_{vj}= 25 ℃		1200		V
I_F	Continuous DC Forward Current			15		A
I_{FRM}	Repetitive Peak Forward Current	t_P=1 ms		30		A
I^2t	I^2t Value	V_R=0 V, t_P=10 ms, T_{vj}=125 ℃		100		A^2s

Characteristics (Diode Brake-Chopper)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage	I_F=15 A, V_{CE}=0 V, T_{vj}=25 ℃		1.9	2.5	V
		I_F=15 A, V_{CE}=0 V, T_{vj}=125 ℃		1.90	2.5	V
t_{rr}	Reverse Recovery time	I_F=15 A,V_R=600 V -di/dt=300A/us T_{vj}=25 ℃		220		ns
Q_r	Recovered Charge			0.8		μC
E_{rec}	Reverse Recovery Energy			0.2		mJ
t_{rr}	Reverse Recovery time	I_F=15A,V_R=600 V -di/dt=300A/us T_{vj}=125 ℃		370		ns
Q_r	Recovered Charge			1.4		μC
E_{rec}	Reverse Recovery Energy			0.4		mJ
R_{thJC}	Thermal resistance, junction to case	I_F=15 A, V_{CE}=0 V, T_{vj}=25 ℃			1.75	K/W
$T_{vj\ op}$	Temperature under switching conditions		-40		125	℃

NTC-Thermistor (Characteristic Values)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated resistance	T_c=25 ℃		5		KΩ
ΔR/R	Deviation of R100	T_c=100 ℃	-5		5	%
P_{25}	Power dissipation	T_c=25 ℃		20		mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298,15K))]$		3380		K
$B_{25/100}$	B-value	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298,15K))]$		3450		K

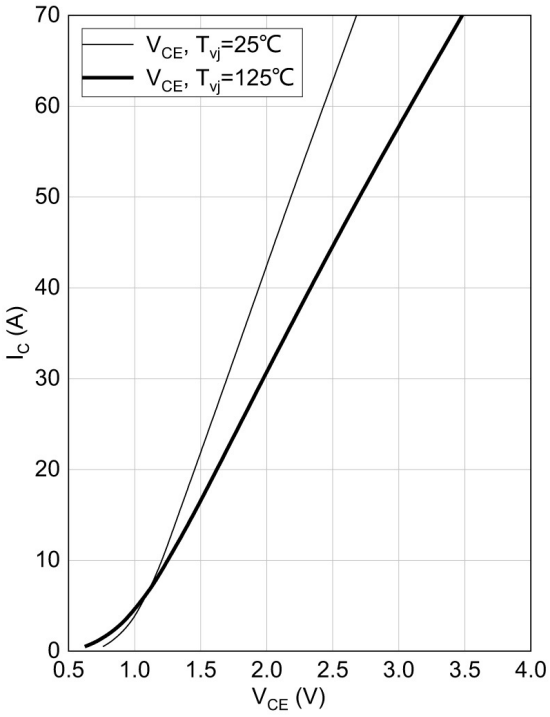
Module Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{isol}	Isolation voltage	t=1min,f=50Hz	2500			V
T_{stg}	Storage Temperature		-40		125	℃
F	Mountig Force per Clamp		40		80	N
G	Weight of Module			40		g

Output characteristic of IGBT,Inverter (typical)

$I_c = f(V_{CE})$

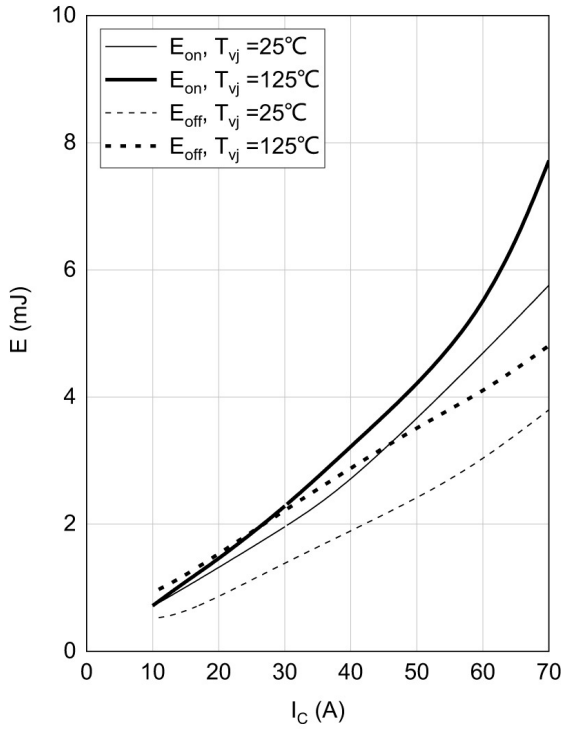
$V_{GE} = 15V$



Switching time of IGBT,Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$

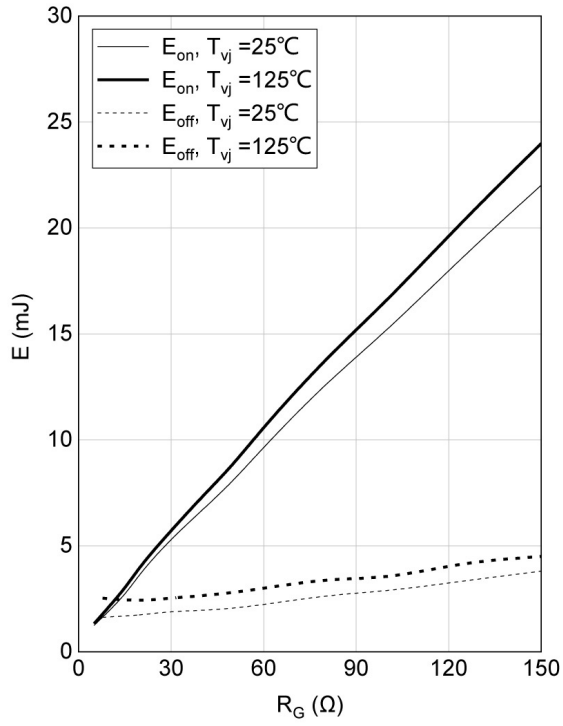
$V_{GE} = \pm 15V$, $R_G = 15\Omega$, $V_{CE} = 600V$



Switching losess of IGBT,Inverter (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$

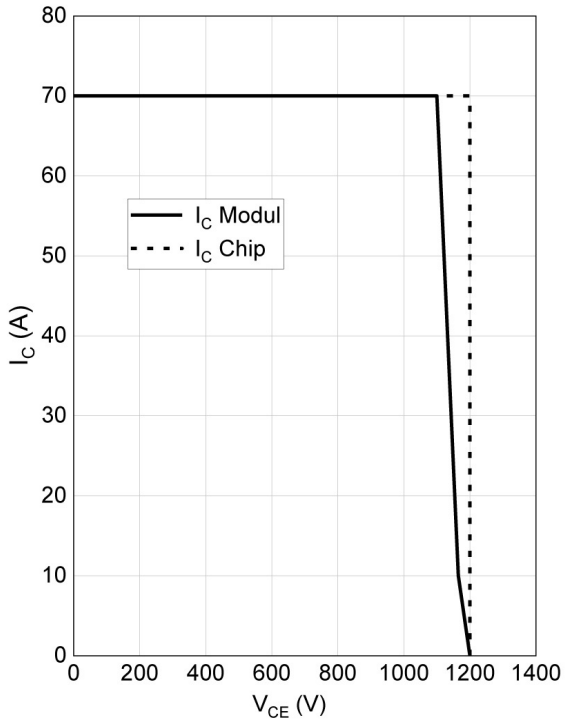
$V_{GE} = \pm 15V$, $I_C = 40A$, $V_{CE} = 600V$



RBSOA IGBT,Inverter (typical)

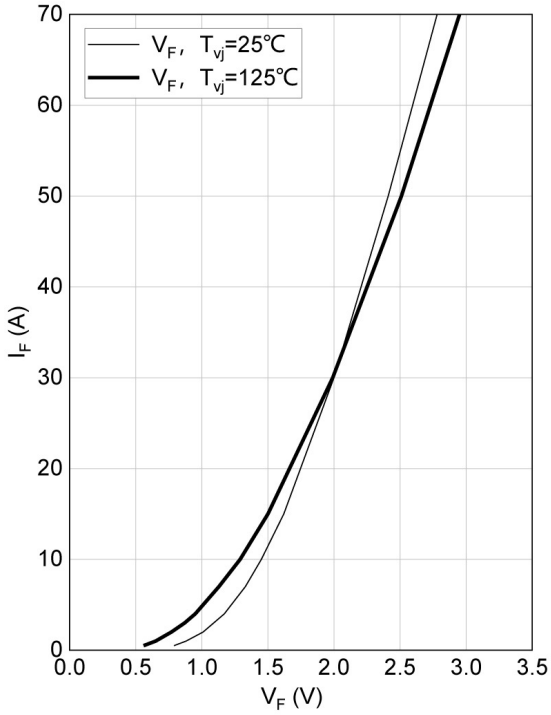
$I_C = f(V_{CE})$

$V_{GE} = \pm 15V$, $R_{Goff} = 15\Omega$, $T_{vj} = 125\,℃$



Forward characteristic of Diode,Inverter (typical)

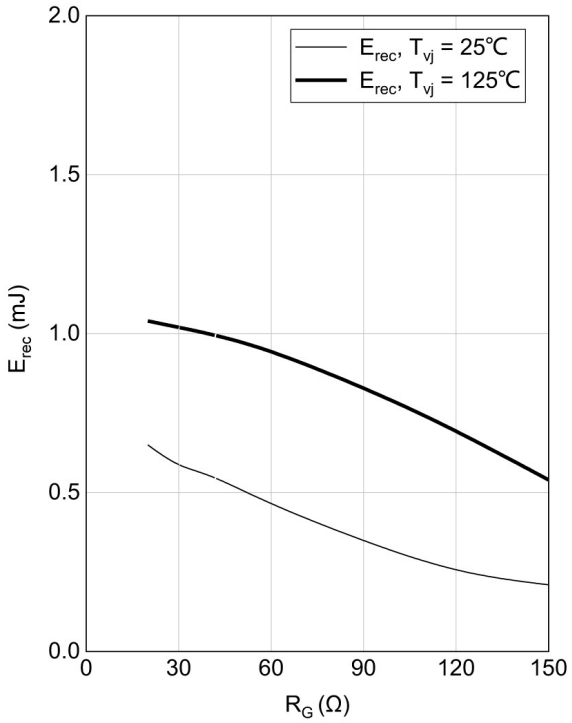
$I_F = f(V_F)$



Switching losses of Diode, Inverter (typical)

$E_{rec} = f(R_G)$,

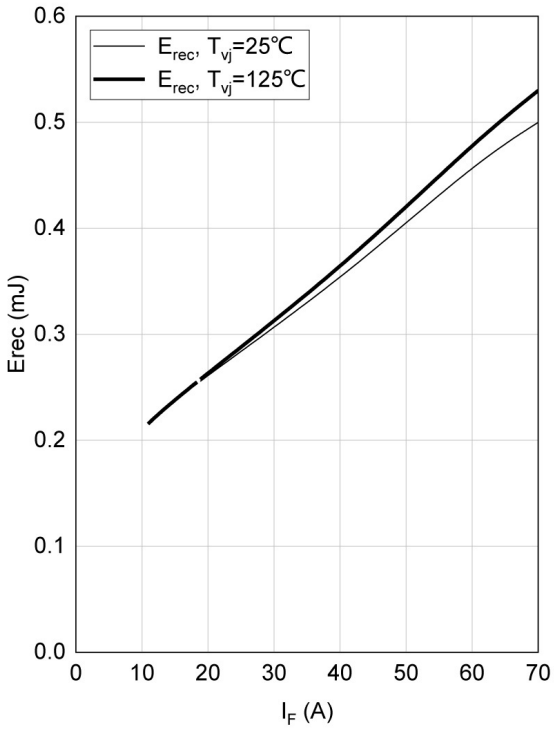
$I_F = 40A$， $V_{CE} = 600V$



Switching losses of Diode, Inverter (typical)

$E_{rec} = f(I_F)$,

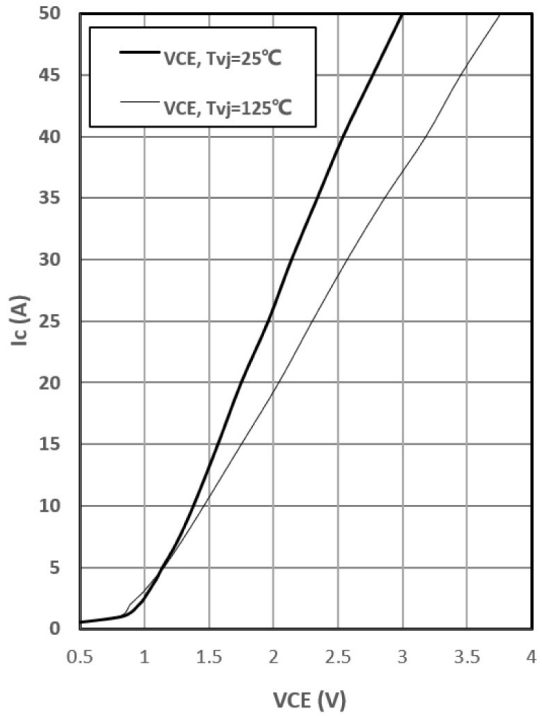
$R_{Gon} = 15\Omega$， $V_{CE} = 600V$



Output characteristic of IGBT,Brake-Chopper, (typical)

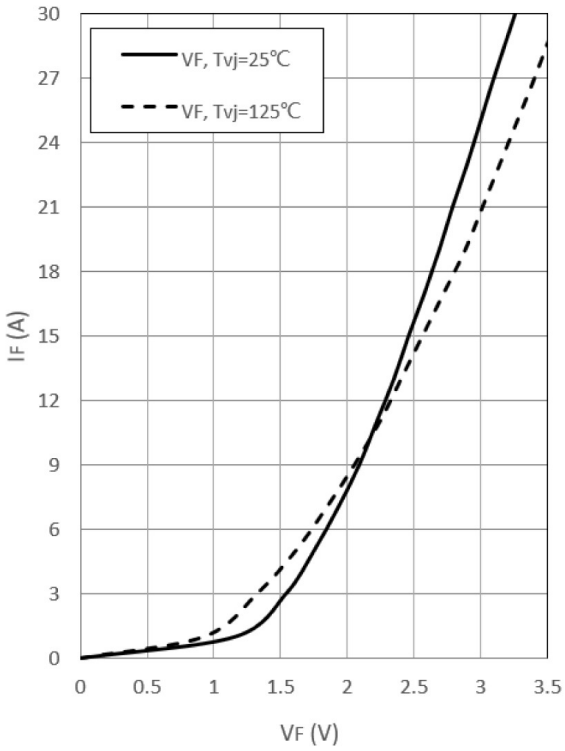
$I_c = f(V_{CE})$

$V_{GE} = 15V$



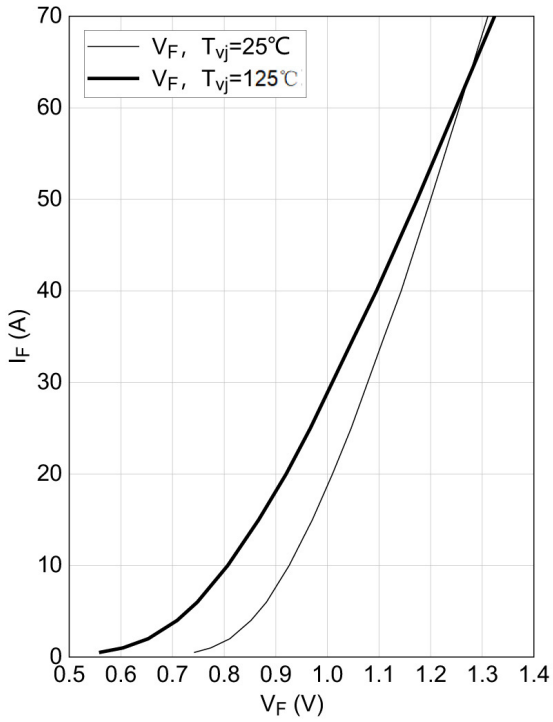
Forward characteristic of Diode,Brake-Chopper (typical)

$I_F = f(V_F)$



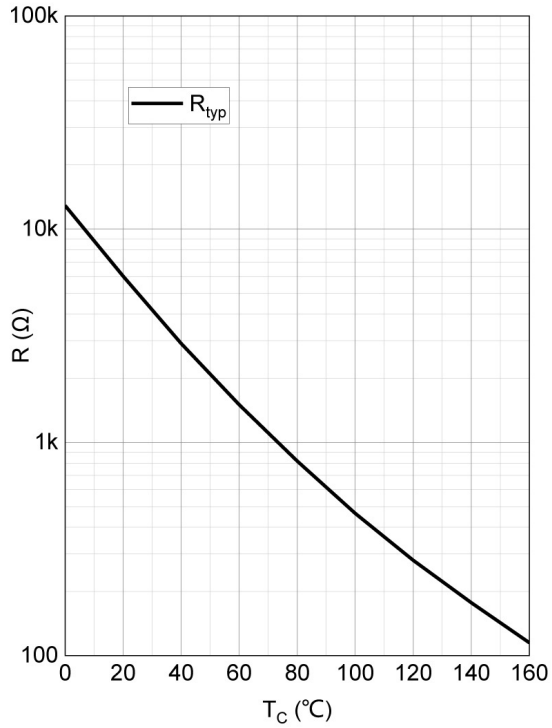
Forward characteristic of Diode, Rectifier(typical)

$I_F = f(V_F)$

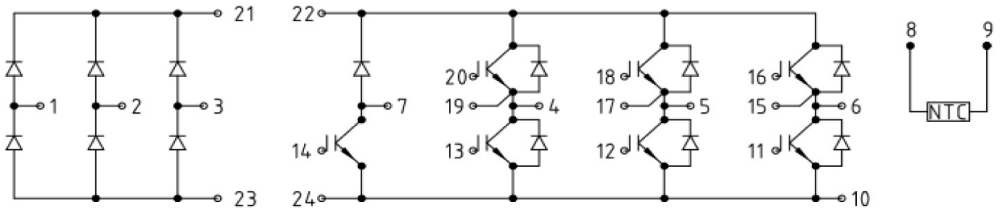


NTC-thermistor-temperature characteristic (typical)

$R = f(T_{NTC})$,



Circuit Diagram



Package Dimensions

(Dimensions in Millimeters)